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Power Matters[™]

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Overview Diagrams

Collector to Emitter Saturation Voltage V _{CE(sat)} 1.00 V DC Current Gain HFE 20.00 100.00	Electrical Rating	Symbol	Min	Тур	Max	Unit
DC Current Gain HFE 20.00 100.00	Collector to Emitter Saturation Voltage	V _{CE(sat)}			1.00	V
	DC Current Gain	HFE	20.00		100.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			60.00	V
Collector Current (dc)	I _C			10.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			60.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			6.00	V
Power Dissipation, Total	P _T			150.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ NPN Transistor

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